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(54) Title: METHOD FOR USING COMPOSITION COMPRISING ORGANIC ACID COMPOUND, LITHOGRAPHY COM-
POSITION COMPRISING ORGANIC ACID COMPOUND, AND METHOD FOR MANUFACTURING RESIST PATTERN

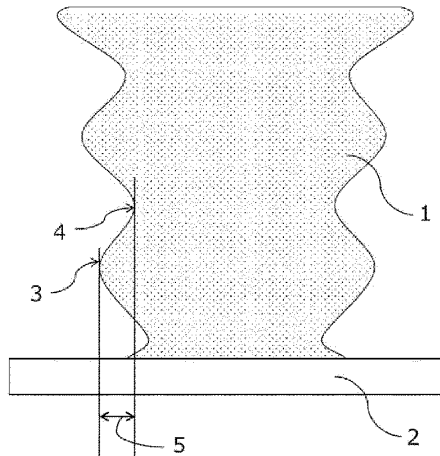


Figure 1

(57) Abstract: [Problem] A method for reducing standing wave in a lithography process is provided. [Means for Solution] A method
for using a composition comprising an organic acid compound (AA) having a certain structure to reduce standing wave in a lithography
process. The distance between the antinode (3) and the node (4) in the direction parallel to the substrate (2) is referred to as the internode
distance (5). The internode distance (5) / desired pattern width is referred to as the standing wave index. By reducing standing wave
that appears in the resist pattern (1), pattern collapse, which is caused due to undesired shape or formation of a notch, is suppressed
and stable formation of a finer pattern is facilitated.

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